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# A 2GHz GaN Class-J Power Amplifier for Base Station Applications

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- # Outline
- PA designer targets
- Traditional approaches
- Introduction to Class-J
- Design methodology
- Realization and measurements
- Conclusions



# • Main drivers

## • GREEN

- Environmental concerns
- Operational expenses

## • SIMPLE

- Deployment costs
- Maintenance

## • FAST

- User experience



In PA words

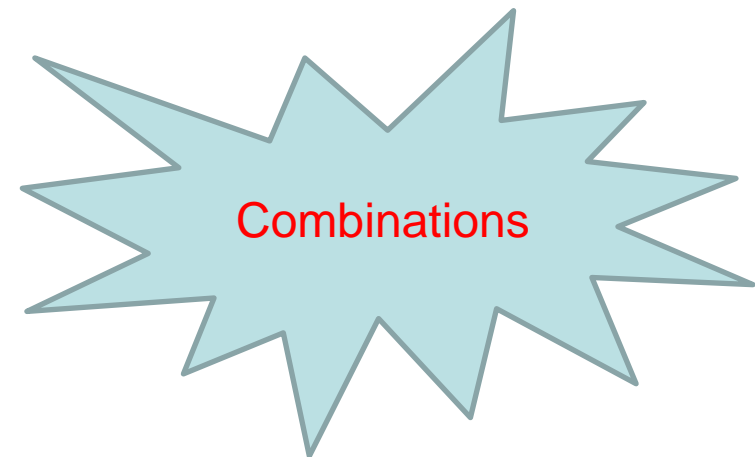
- Efficiency
- Linearity
- Bandwidth



Which one is more important?

# • Traditional approaches

- Power Amplifier
  - Linear amplifiers
  - Switching amplifiers
  - Harmonically tuned
- System level
  - Doherty
  - Envelope Elimination & Restoration (EER)
  - Envelope tracking (ET)
  - Digital Pre-distortion



- **Class J theory (1)**
- Recently introduced – explains widely observed results
- Under harmonically tuned category (up to second harmonic)
- Better control of trade-offs
- **Highly efficient**
- **Quasi-linear**
- Super-set of Class-B operation

**GREEN**

**SIMPLE**

**WIDEBAND**

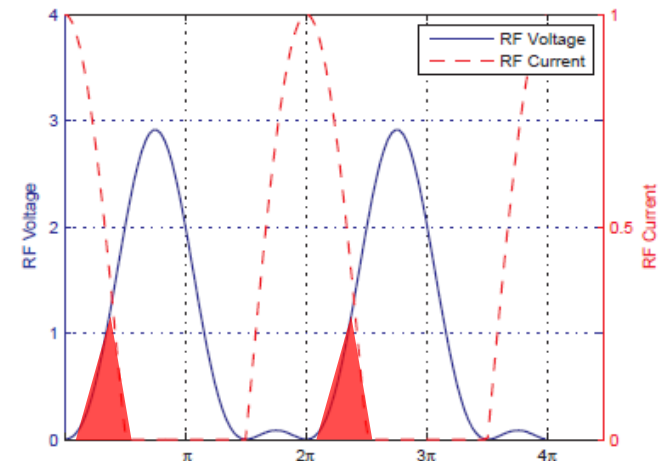


# • Class J theory (2)

- Biased as Class-B, deep AB
- Second harmonic not shorted (purely reactive)
- Complex fundamental impedance
- No “knee” voltage crossing occurs
- Same efficiency/output power as Class-B
- Large drain voltage swing almost 3x supply voltage

$$Z_{f_0} = 1.4142 \angle 45^\circ$$

$$Z_{2f_0} = 1.1781 \angle -90^\circ$$



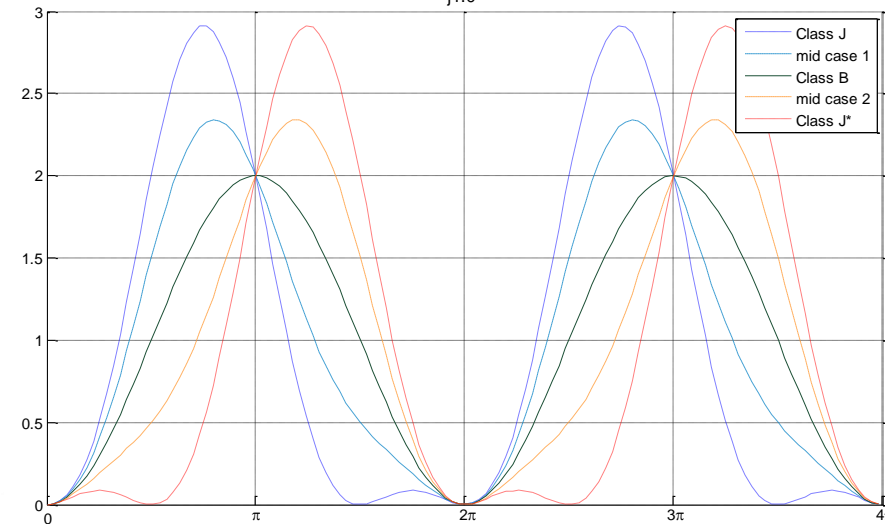
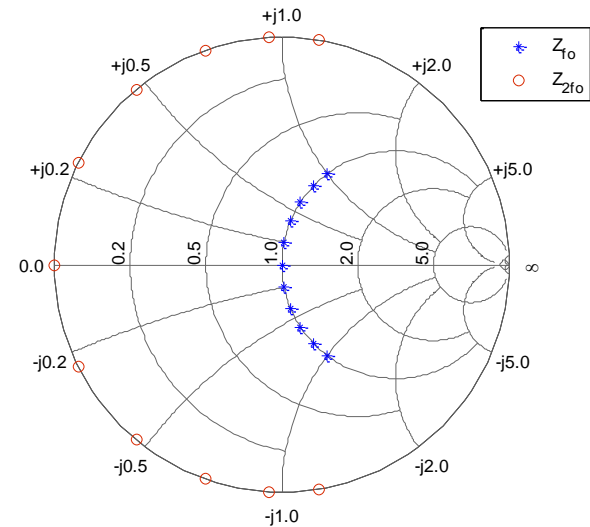
# • Class J theory (3)

- Design space is continuous
- All cases have same efficiency/output power

$$Z_{f_0} = \frac{\pi \sqrt{1 + d^2} (1 - \cos \frac{\alpha}{2})}{a - \sin \alpha} \angle \text{atan} \left( -\frac{1}{d} \right) + \varphi$$

$$\varphi = \begin{cases} \frac{\pi}{2}, & d \geq 0 \\ -\frac{\pi}{2}, & d < 0 \end{cases}$$

$$Z_{2f_0} = \frac{d}{2} \frac{\pi(1 - \cos \frac{\alpha}{2})}{\sin \frac{\alpha}{2} - \frac{1}{3} \sin \frac{3\alpha}{2}} \angle -\frac{\pi}{2}$$





# • Methodology

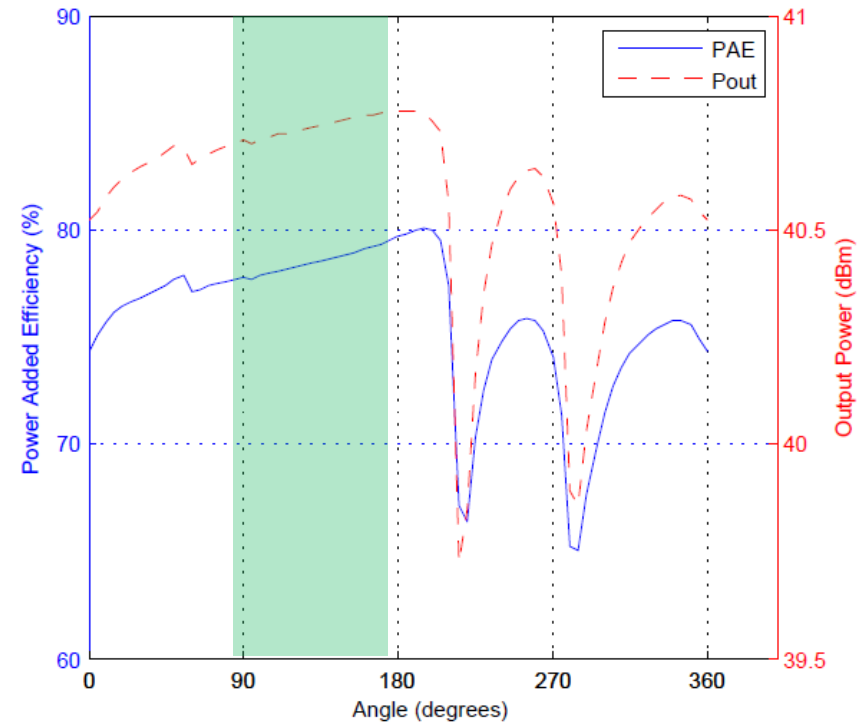
- Large signal transistor model
    - 10W GaN HEMT device
  - Transistor extrinsic parasitics model
    - Linear output capacitance
  - Class J theory
    - Impedances at the intrinsic drain
1. Deep Class - AB biasing
  2. Determine appropriate load-line
  3. Intrinsic drain impedances based on theory
  4. 3<sup>rd</sup> output harmonic impedance
  5. Source-pull for efficiency/gain
  6. Observe intrinsic drain waveforms
  7. Design matching networks



# • 3<sup>rd</sup> output harmonic

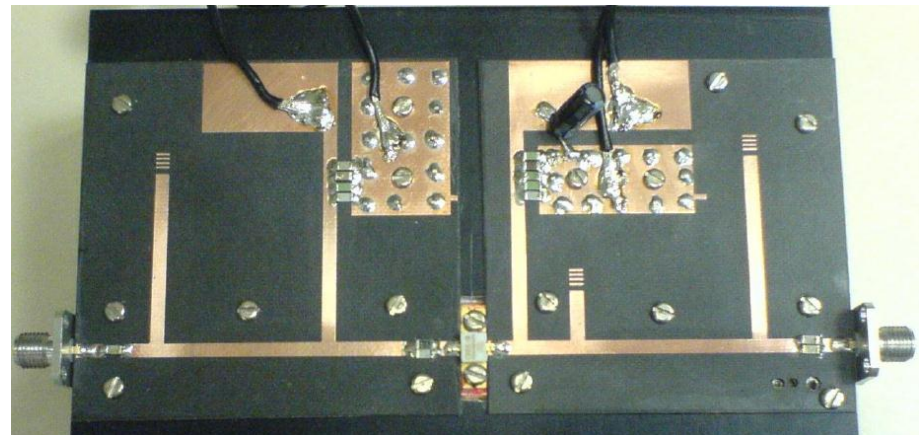
- Class J theory defines fundamental and second harmonic terminations
- Class B biasing assumed
- Perfect half-rectified sine wave drain current (no 3<sup>rd</sup> harmonic)

**IN PRACTICE?**

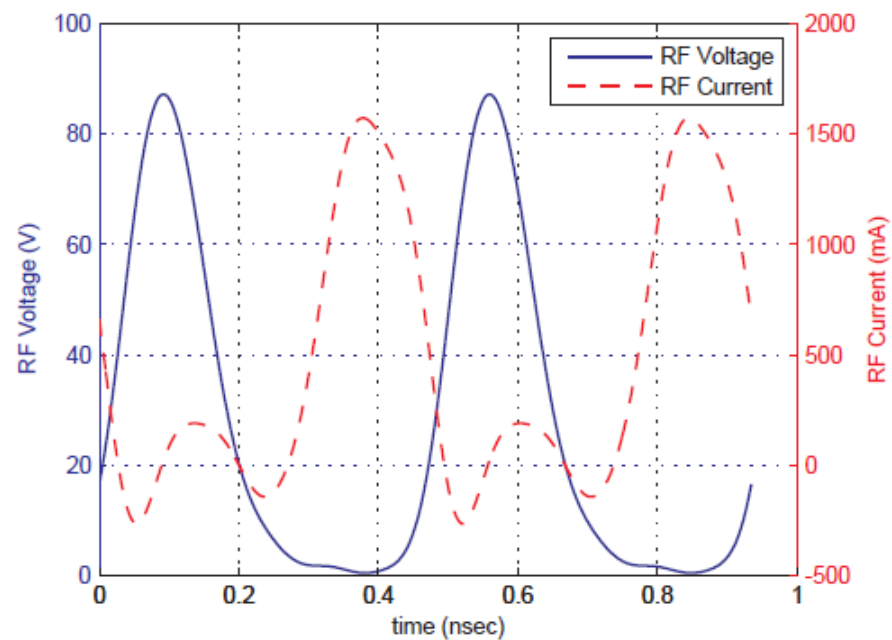
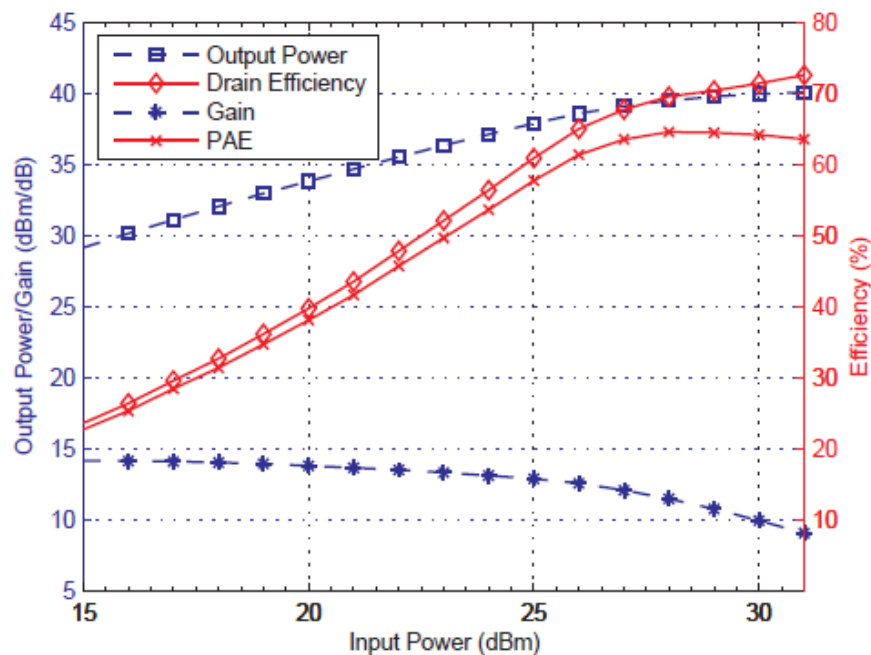


# • PA realisation

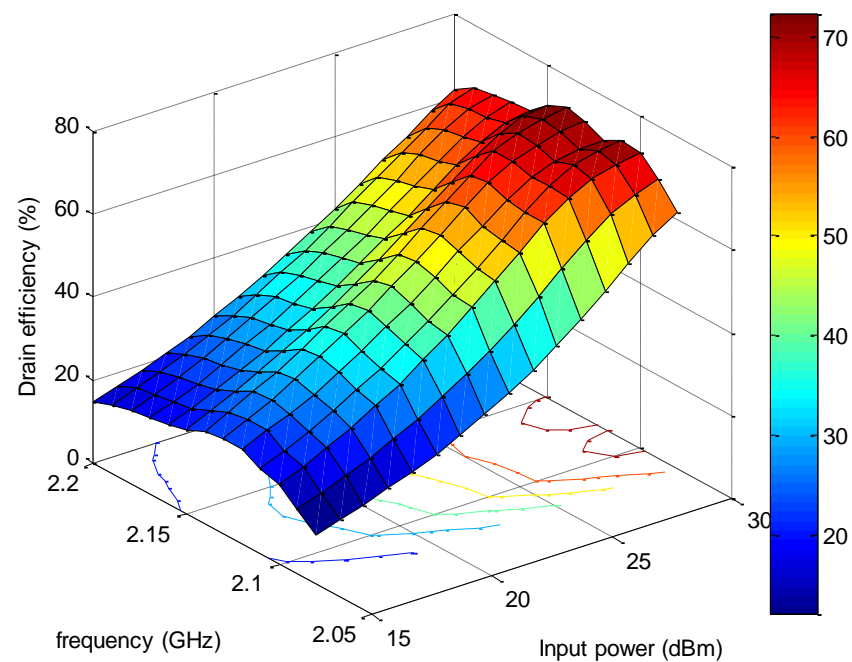
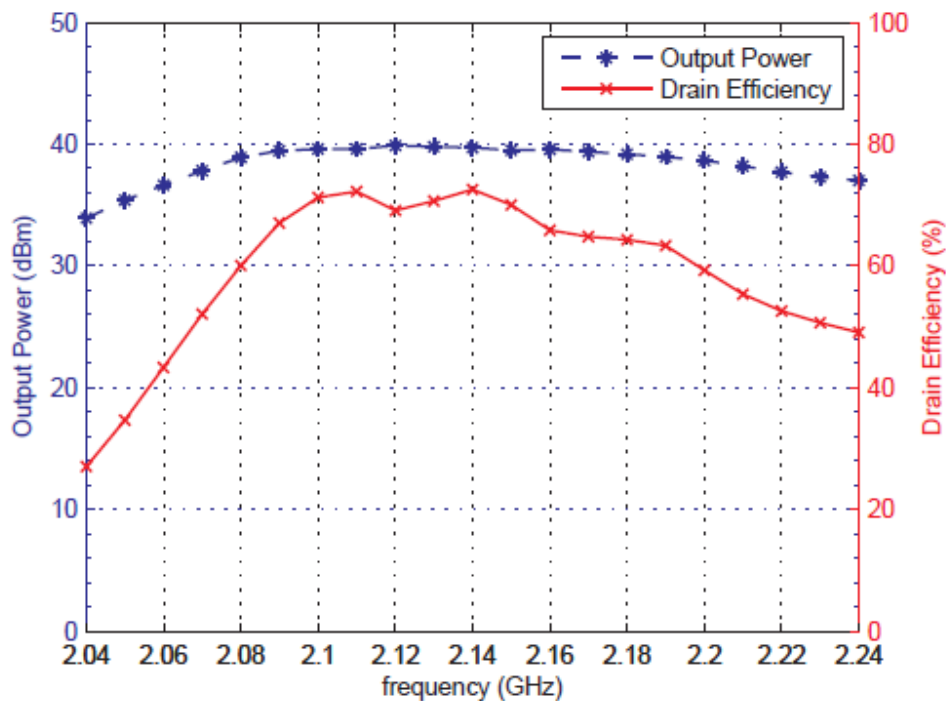
- Input stabilization network
- Harmonic control
  - Two at the input
  - Three at the output
- RT-Duroid 8550 substrate
  - $E_r = 2.2$
  - $T = 0.787$  mm
- Fully distributed architecture
- Size : 13.5 x 6.5 cm



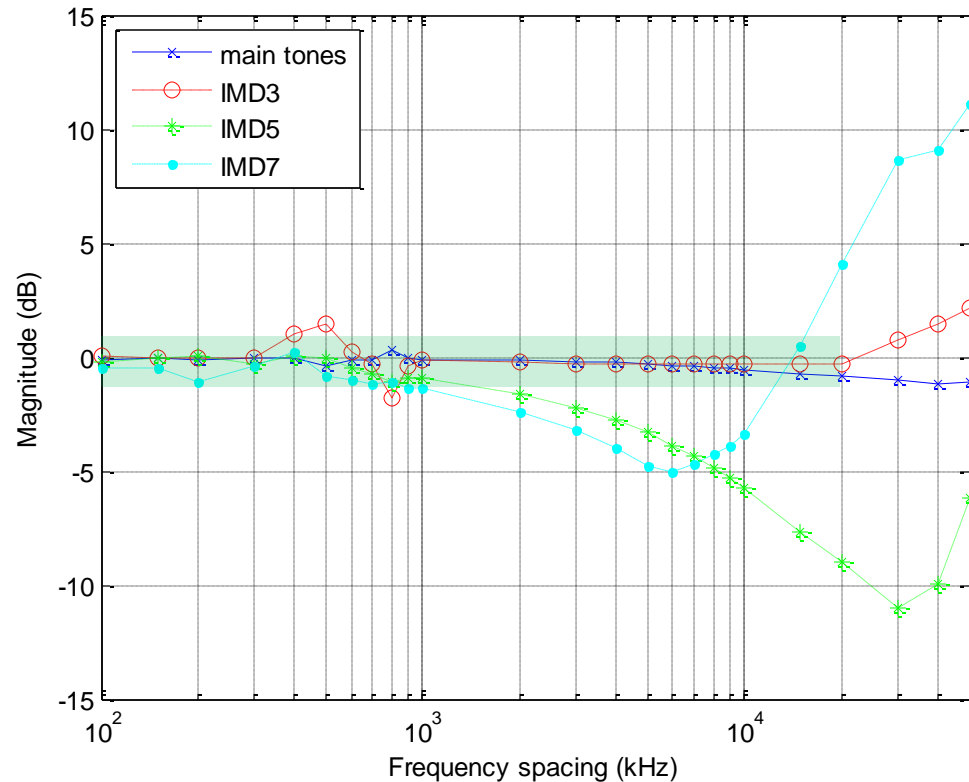
# • Input power sweep



- Over frequency

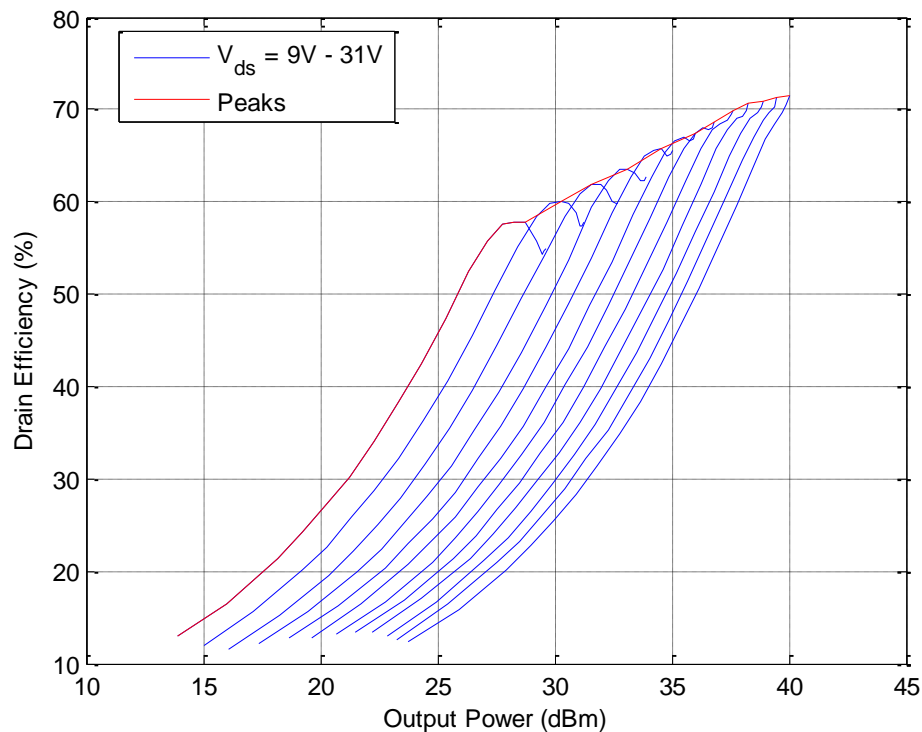


# • Two tone measurements



- Typical measure of memory effects
- Asymmetry between upper/lower channels
- Each tone 24dBm
- Variable spacing (100kHz-50MHz)
- Low memory effects up to 20MHz

# • Variable $V_{DS}$



- Good potential under ET/EER
- $V_{DS}$  can go lower (approx. 4-5V)
- 15dB output power back-off
- Modulator efficiency

# • Conclusions

- New tool for management of efficiency/linearity/bandwidth tradeoffs
- More freedom in PA design / no need for harmonic short
- Theory and extrinsic parasitic model is sufficient
- 3<sup>rd</sup> harmonic is important
- Low memory effects
- Very promising for ET/EER implementations







Thank You

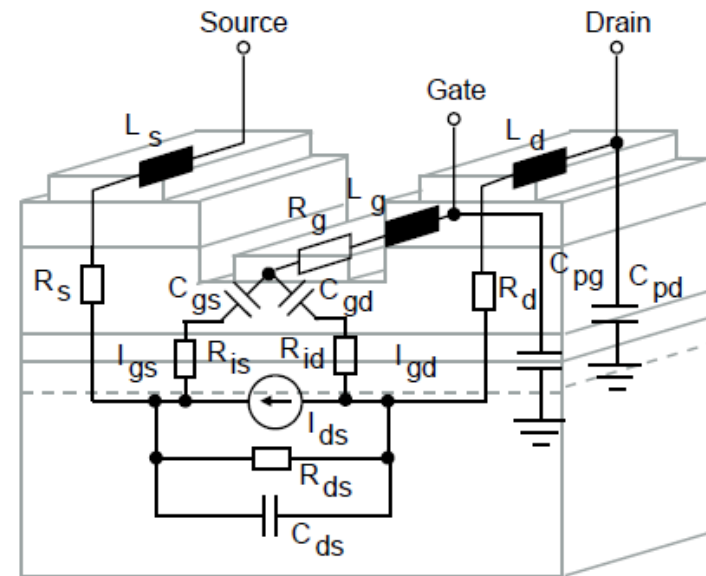
QUESTIONS?



# APPENDIX

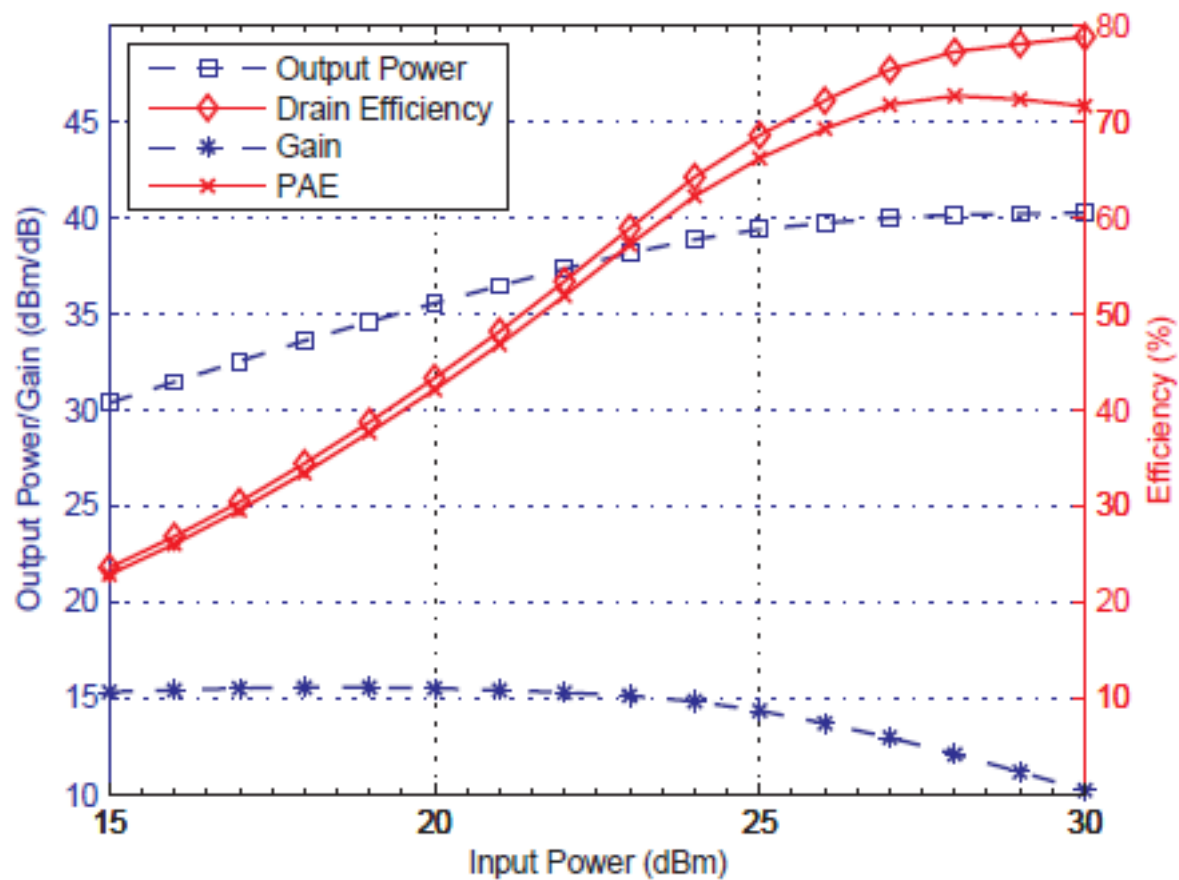
## HEMTs

- Current generator plane is of interest
- $C_{ds}$  is important
- An appreciation of parasitics is needed
- Package contribution is dominant



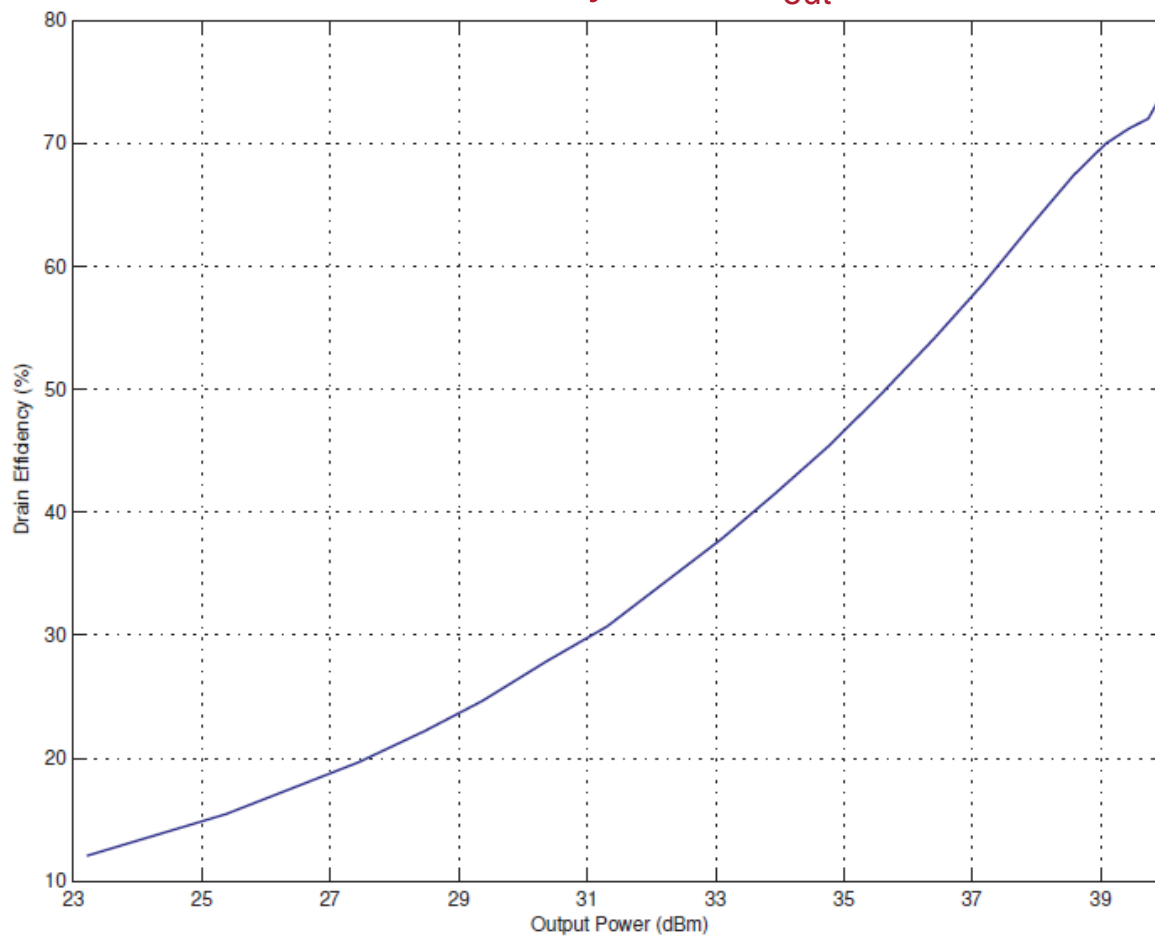
# APPENDIX

## simulation results



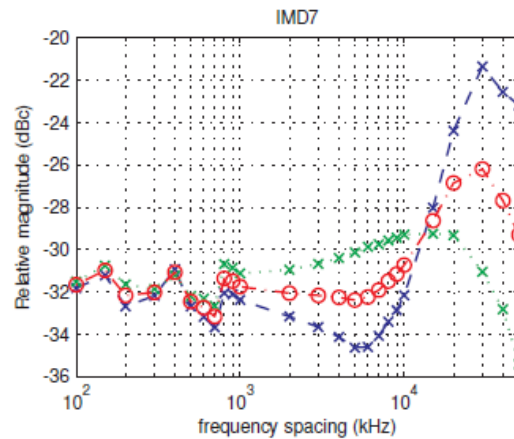
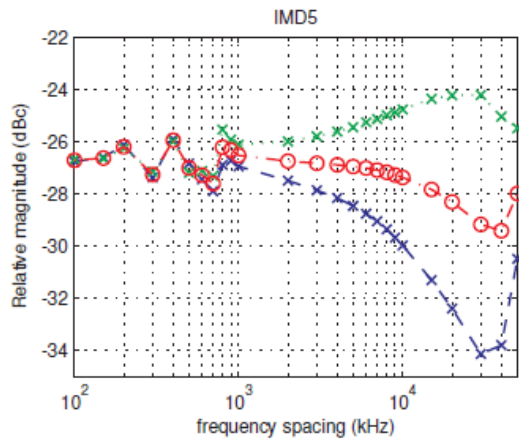
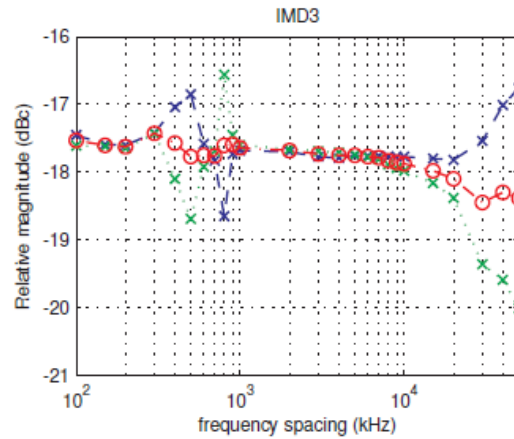
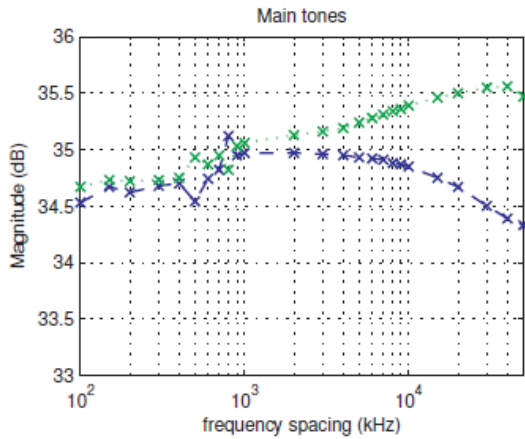
# APPENDIX

measured efficiency over  $P_{out}$



# APPENDIX

## two tone measurements (24dBm)



# APPENDIX

## two tone measurements (4MHz spacing)

